
2SD2247

Silicon NPN Epitaxial

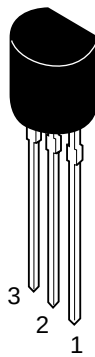
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Application

Low frequency amplifier

Outline

TO-92 (1)



- 1. Emitter
- 2. Collector
- 3. Base

Absolute Maximum Ratings (Ta = 25°C)

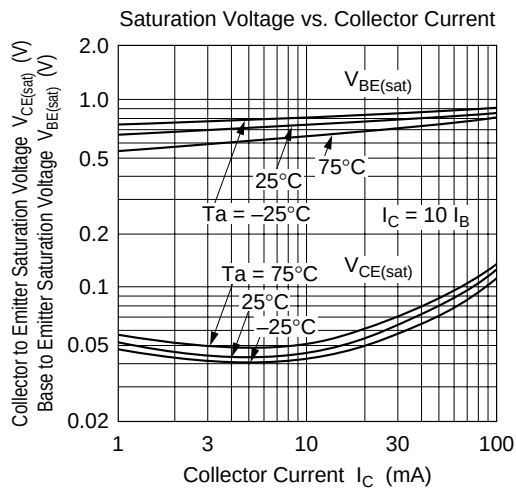
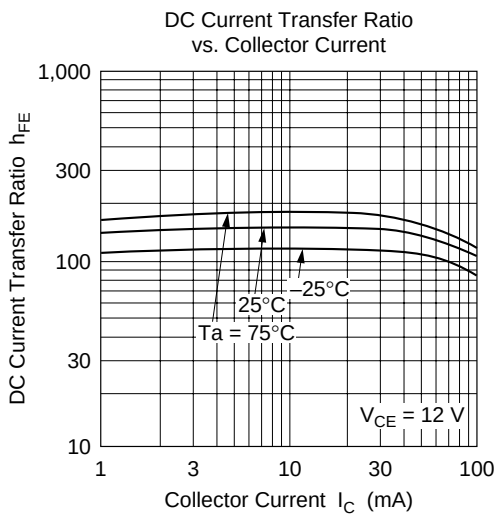
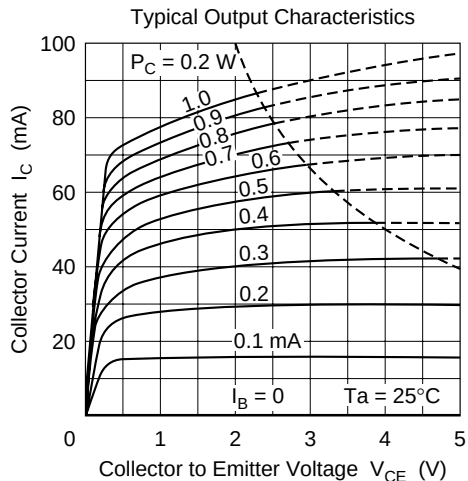
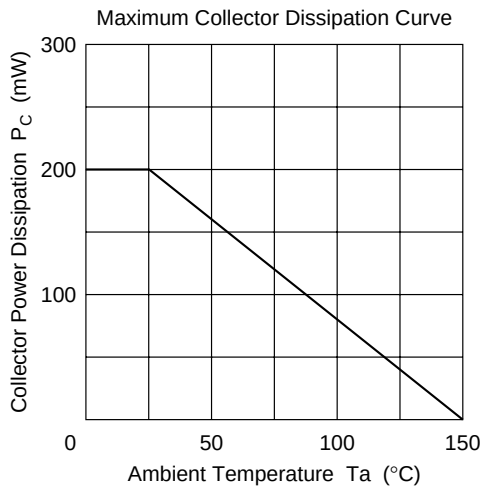
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	55	V
Collector to emitter voltage	V_{CEO}	50	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Emitter current	I_E	−100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

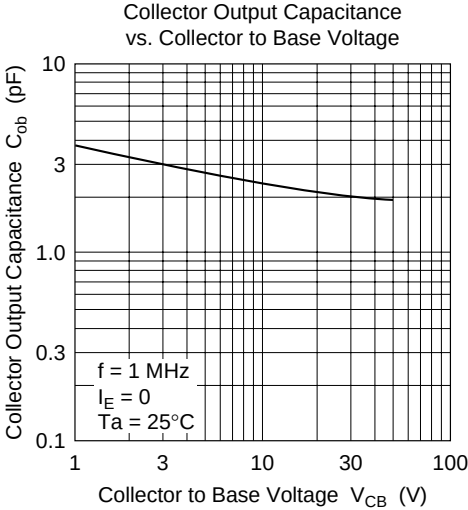
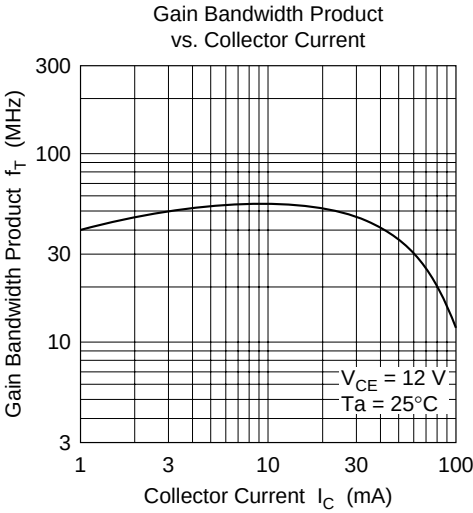
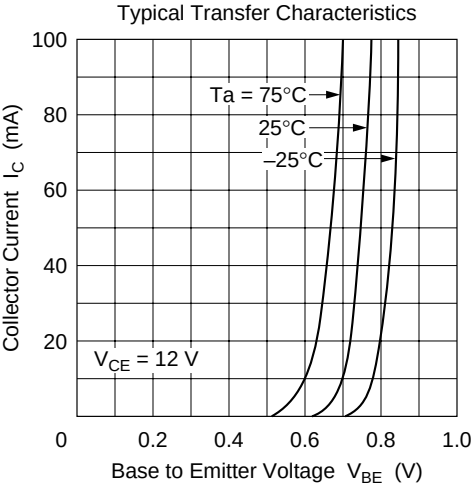
Electrical Characteristics (Ta = 25°C)

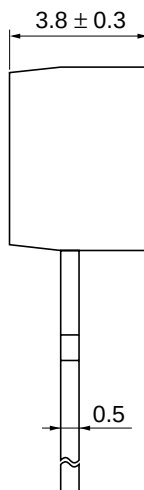
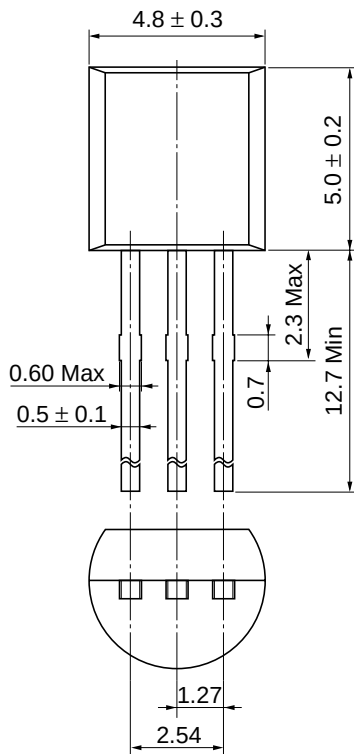
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	55	—	—	V	$I_C = 10\text{ }\mu\text{A}$, $I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	50	—	—	V	$I_C = 1\text{ mA}$, $R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 10\text{ }\mu\text{A}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 40\text{ V}$, $I_E = 0$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB} = 4\text{ V}$, $I_C = 0$
DC current transfer ratio	h_{FE}^{*1}	100	—	320		$V_{CE} = 12\text{ V}$, $I_C = 2\text{ mA}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	0.2	V	$I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$
Base to emitter voltage	V_{BE}	—	0.67	0.75	V	$V_{CE} = 12\text{ V}$, $I_C = 2\text{ mA}$
Gain bandwidth product	f_T	—	—	100	Mhz	$V_{CE} = 12\text{ V}$, $I_C = 2\text{ mA}$
Collector output capacitance	C_{ob}	—	1.8	3.5	pF	$V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$

Note: 1. The 2SD2247 is grouped by h_{FE} as follows.

Grade	B	C
h_{FE}	100 to 200	160 to 320







Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.25 g

Cautions

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